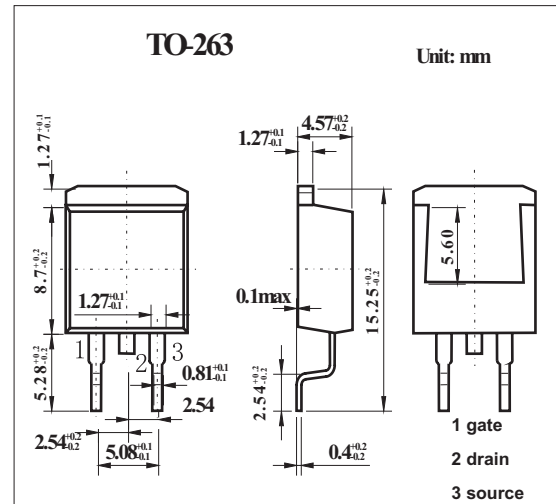
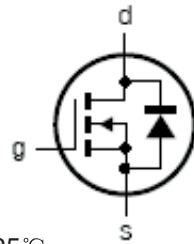


TrenchMOS™ standard level FET

KUK7607-30B

■ Features

- Very low on-state resistance
- Q101 compliant
- 175°C rated
- Standard level compatible.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	30	V
Drain-gate voltage $R_{GS} = 20\text{ K}\Omega$	V_{DGR}	30	V
Gate-source voltage	V_{GS}	± 20	V
Drain current (DC) $T_{mb} = 25^\circ\text{C}, V_{GS} = 10\text{ V}$	I_D	108	A
Drain current (DC) $T_{mb} = 100^\circ\text{C}, V_{GS} = 10\text{ V}$	I_D	75	A
Drain current (pulse peak value) *1	I_{DM}	435	A
Total power dissipation $T_{mb} = 25^\circ\text{C}$	P_{tot}	157	W
Storage & operating temperature	T_{stg}, T_j	-55 to 175	$^\circ\text{C}$
reverse drain current (DC) $T_{mb} = 25^\circ\text{C}$	I_{DR}	108	A
		75	A
pulsed reverse drain current *1	I_{DRM}	435	A
non-repetitive avalanche energy *2	$E_{DS(AL)S}$	329	J
Thermal resistance junction to mounting base	$R_{th\ j-mb}$	0.95	K/W
Thermal resistance junction to ambient	$R_{th\ j-a}$	50	K/W

* 1 $T_{mb} = 25^\circ\text{C}$; pulsed; $t_p \leq 10\ \mu\text{s}$;

*2 unclamped inductive load; $I_D = 75\text{ A}$; $V_{DS} \leq 30\text{ V}$; $V_{GS} = 10\text{ V}$; $R_{GS} = 50\ \Omega$; starting $T_{mb} = 25^\circ\text{C}$

KUK7607-30B

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$	30			V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55^\circ\text{C}$	27			V
gate-source threshold voltage	$V_{GS(th)}$	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25^\circ\text{C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175^\circ\text{C}$	1			V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55^\circ\text{C}$			4.4	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$		0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175^\circ\text{C}$			500	μA
gate-source leakage current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		2	100	nA
drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25^\circ\text{C}$..	5.9	7	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175^\circ\text{C}$			13.3	m Ω
total gate charge	$Q_{g(tot)}$			36		nC
gate-to-source charge	Q_{gs}	$V_{GS} = 10 \text{ V}; V_{DD} = 24 \text{ V}; I_D = 25 \text{ A}$		9		nC
gate-to-drain (Miller) charge	Q_{gd}			12		nC
input capacitance	C_{iss}			1820	7446	pF
output capacitance	C_{oss}	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}$		632	1014	pF
reverse transfer capacitance	C_{rss}			256	360	pF
turn-on delay time	$t_{d(on)}$	$V_{DD} = 25 \text{ V}; R_L = 1.2\Omega; V_{GS} = 10 \text{ V}; R_G = 10\Omega$		20		ns
rise time	t_r			51		ns
turn-off delay time	$t_{d(off)}$			51		ns
fall time	t_f			44		ns
internal drain inductance	L_d		from drain lead 6 mm from package to centre of die		4.5	
				2.5		nH
internal source inductance	L_s	from source lead to source bond pad		7.5		nH
source-drain (diode forward) voltage	V_{SD}	$I_s = 40\text{A}; V_{GS} = 0 \text{ V}$		0.85	1.2	V
reverse recovery time	t_{rr}	$I_s = 25 \text{ A}; -di_F/dt = -100 \text{ A}/\mu\text{s};$		46		ns
recovered charge	Q_r	$V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}$		28		nC